TC74HC4049AP/AF/AFN
TC74HC4050AP/AF/AFN

TC74HC4049 HEX Buffer Converter (Inverting)
TC74HC4050 HEX Buffer Converter

The TC74HC4049A and TC74HC4050A are high speed CMOS HEX BUFFERs fabricated with silicon gate C^2MOS technology.

They achieve the high speed operation similar to equivalent LSTTL while maintaining the CMOS low power dissipation.

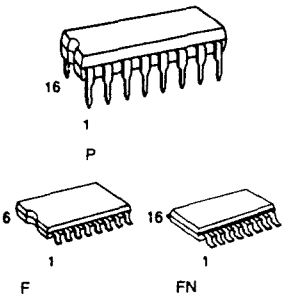
The TC74HC4049A is an inverting buffer, while the TC74HC4050A is a non-inverting buffer. The internal circuits are composed of 3-stages (HC4049A) or 2-stages (HC4050A) of inverters, which provide high noise immunity and stable output.

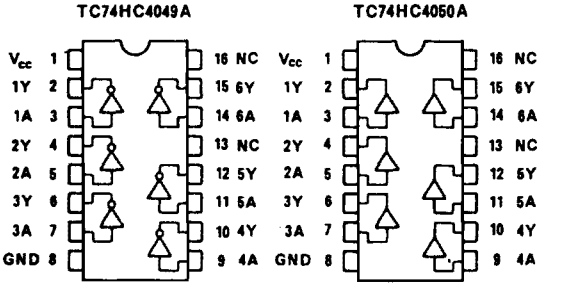
Input protection circuits are different from those of other high speed CMOS ICs. They eliminate the diodes on the V_{CC} side thus providing of logic-level conversion from high-level voltages up to 15V to low-level voltages.

They are useful for battery back up circuits, because input voltage can be applied on ICs which are not biased by V_{CC}.

Features

- High Speed: t_{pd} = 9ns(Typ.) at V_{CC} = 5V
- Low Power Dissipation: I_{CC} = 1μA(Max.) at Ta = 25°C
- High Noise Immunity: $V_{NIH} = V_{NIL}$ = 28% V_{CC}(Min.)
- Output Drive Capability: 15 LSTTL Loads
- Symmetrical Output Impedance: $|I_{OH}| = I_{OL}$ = 6mA(Min.)
- Balanced Propagation Delays: $t_{pLH} = t_{pHL}$
- Wide Operating Voltage Range: V_{CC}(opr) = 2V ~ 6V
- Pin and Function Compatible with 4049B/4050B





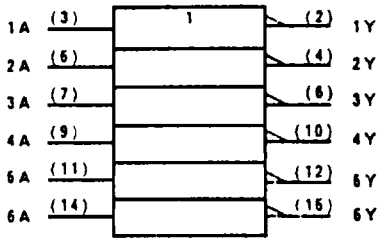
(Top View) NC : No Connection

Pin Assignment

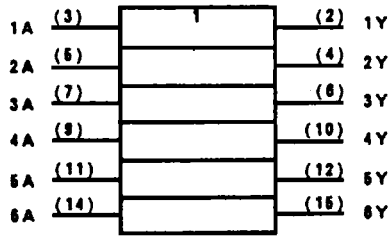
Truth Table

A	Y(4049A)	Y(4050A)
L	H	L
H	L	H

TC74HC4049A

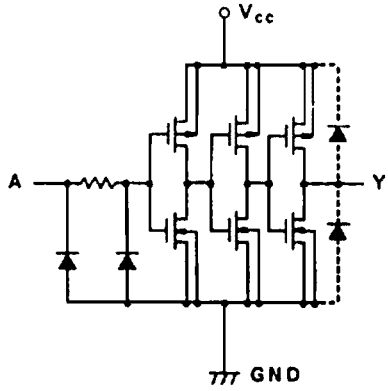


TC74HC4050A

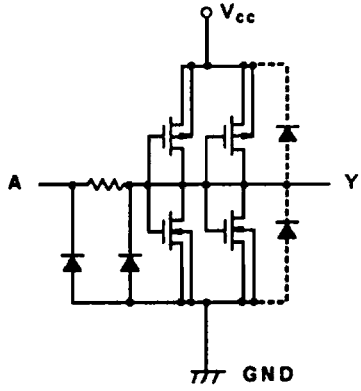


IEC Logic Symbol

TC74HC4049A



TC74HC4050A



Input and Output Equivalent Circuit

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Supply Voltage Range	V_{CC}	-0.5 ~ 7	V
DC Input Voltage	V_{IN}	-0.5 ~ 18*	V
DC Output Voltage	V_{OUT}	-0.5 ~ V_{CC} + 0.5	V
Input Diode Current	I_{IK}	±20	mA
Output Diode Current	I_{OK}	±20	mA
DC Output Current	I_{OUT}	±25	mA
DC V_{CC}/Ground Current	I_{CC}	±50	mA
Power Dissipation	P_D	500(DIP)*/180(SOIC)	mW
Storage Temperature	T_{stg}	-65 ~ 150	°C
Lead Temperature 10sec	T_L	300	°C

Note) * DC input voltage (V_{IN}) specified is measured to GND and is not related to V_{CC}.
Recommended operating range is 0V to 15V and it is possible to convert logic-levels from 15V to 5V or 5V to 2V.
* 500mW in the range of Ta = -40°C ~ 65°C. From Ta = 65°C to 85°C a derating factor of -10mW/°C shall be applied until 300mW.

Recommended Operating Conditions

Parameter	Symbol	Value	Unit
Supply Voltage	V_{CC}	2 ~ 6	V
Input Voltage	V_{IN}	0 ~15	V
Output Voltage	V_{OUT}	0 ~ V_{CC}	V
Operating Temperature	T_{opr}	-40 ~ 85	°C
Input Rise and Fall Time	t_r, t_f	0 ~ 1000(V_{CC} = 2.0V) 0 ~ 500(V_{CC} = 4.5V) 0 ~ 400(V_{CC} = 6.0V)	ns

DC Electrical Characteristics

Parameter	Symbol	Test Condition			Ta = 25°C			Ta = -40 ~ 85°C		Unit
				V_{CC}	Min	Typ.	Max.	Min.	Max.	
High-Level Input Voltage	V_{IH}	–		2.0 4.5 6.0	1.5 3.15 4.2	– – –	– – –	1.5 3.15 4.2	– – –	V
Low-Level Input Voltage	V_{IL}	–		2.0 4.5 6.0	– – –	– – –	0.5 1.35 1.8	– – –	0.5 1.35 1.8	V
High-Level Output Voltage	V_{OH}	V_{IN} = V_{IH} or V_{IL}	I_{OH} = -20μA	2.0 4.5 6.0	1.9 4.4 5.9	2.0 4.5 6.0	– – –	1.9 4.4 5.9	– – –	V
			I_{OH} = -6 mA I_{OH} = -7.8mA	4.5 6.0	4.18 5.68	4.31 5.80	– –	4.13 5.63	– –	
Low-Level Output Voltage	V_{OL}	V_{IN} = V_{IH} or V_{IL}	I_{OL} = 20μA	2.0 4.5 6.0	– – –	0.0 0.0 0.0	0.1 0.1 0.1	– – –	0.1 0.1 0.1	V
			I_{OL} = 6 mA I_{OL} = 7.8mA	4.5 6.0	– –	0.17 0.18	0.26 0.26	– –	0.33 0.33	
Input Leakage Current	I_{IN}	V_{IN} = V_{CC} or GND		6.0	–	–	±0.1	–	±1.0	μA
Quiescent Supply Current	I_{CC}	V_{IN} = V_{CC} or GND		6.0	–	–	1.0	–	10.0	

AC Electrical Characteristics (C_L = 50pF, Input $t_r = t_f$ = 6ns)

Parameter	Symbol	Test Condition			Ta = 25°C			Ta = -40 ~ 85°C		Unit
			CL	V_{CC}	Min	Typ.	Max.	Min.	Max.	
Output Transition Time	t_{TLH} t_{THL}	–	50	2.0 4.5 6.0	– – –	25 6 5	60 12 10	– – –	75 15 13	ns
Propagation Delay Time	t_{pLH} t_{pHL}	–	50	2.0 4.5 6.0	– – –	30 10 8	75 15 13	– – –	95 19 16	
			150	2.0 4.5 6.0	– – –	45 15 13	100 20 17	– – –	145 29 25	
Input Capacitance	C_{IN}	–			–	5	10	–	10	pF
Power Dissipation Capacitance	C_{PD}(1)	–			–	26	–	–	–	

Note (1) C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation:

$I_{CC(opr)} = C_{PD} \bullet V_{CC} \bullet f_{IN} + I_{CC}/6$(per Gate)